

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## FR101W THRU FR107W

Product specification

**FEATURES**

- Ideal for surface mount applications
- Easy pick and place
- Built-in strain relief
- Fast switching speed

**VOLTAGE RANGE**



50 to 1000 Volts

**CURRENT**

1.0 Ampere

**MECHANICAL DATA**

- Case: Molded plastic
- Epoxy: UL 94V-0 rate flame retardant
- Metallurgically bonded construction
- Polarity: Color band denotes cathode end
- Mounting position: Any

PACKAGE OUTLINE	PIN CONFIGURATION
 SOD-123FL	 1.Cathode 2.Anode

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Rating 25 C ambient temperature unless otherwise specified.  
 Single phase half wave, 60Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

TYPE NUMBER	FR101W	FR102W	FR103W	FR104W	FR105W	FR106W	FR107W	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta=25 C	1.0							A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	30							A
Maximum Instantaneous Forward Voltage at 1.0A	1.3							V
Maximum DC Reverse Current Ta=25°C	5.0							µA
at Rated DC Blocking Voltage Ta=100°C	100							µA
Maximum Reverse Recovery Time (Note 1)	150				250	500		nS
Typical Junction Capacitance (Note 2)	15							pF
Typical Thermal Resistance R JA (Note 3)	80							°C/W
Operating and Storage Temperature Range Tj, Tstg	-65 — +150							°C
Marking Code								

- NOTES:**
1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
  2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
  3. Thermal Resistance from Junction to Ambient.

**RATING AND CHARACTERISTIC CURVES FR101W THRU FR107W**

FIG.1-TYPICAL FORWARD CHARACTERISTICS

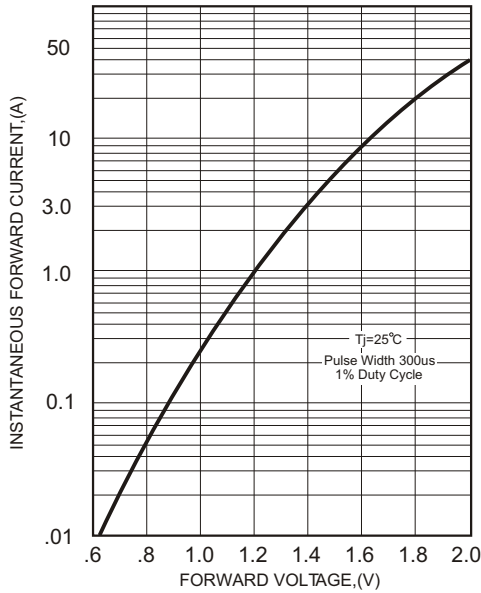


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

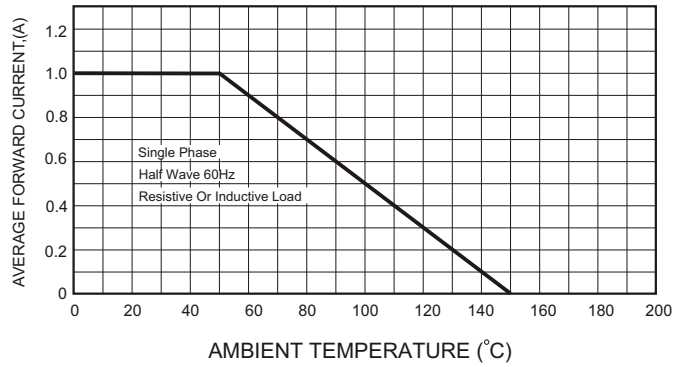


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

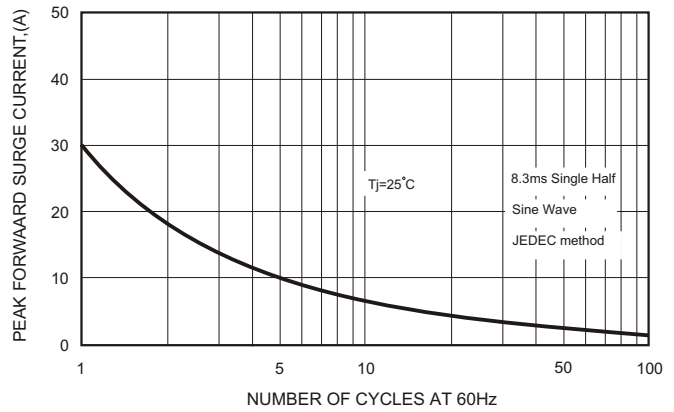
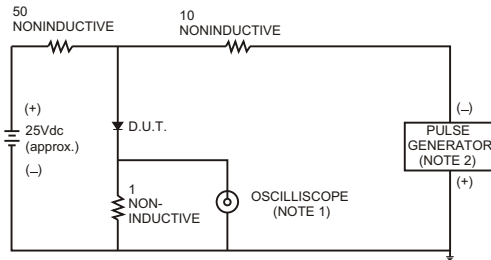


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



- NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm, 22pF.  
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

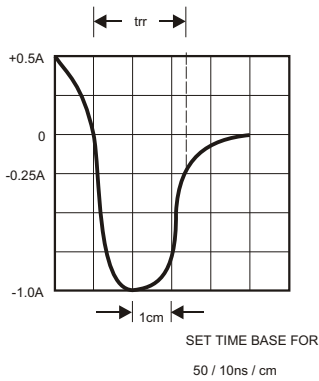
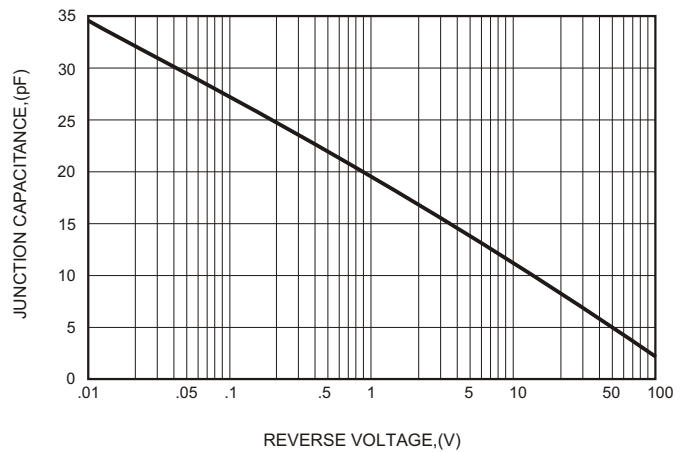
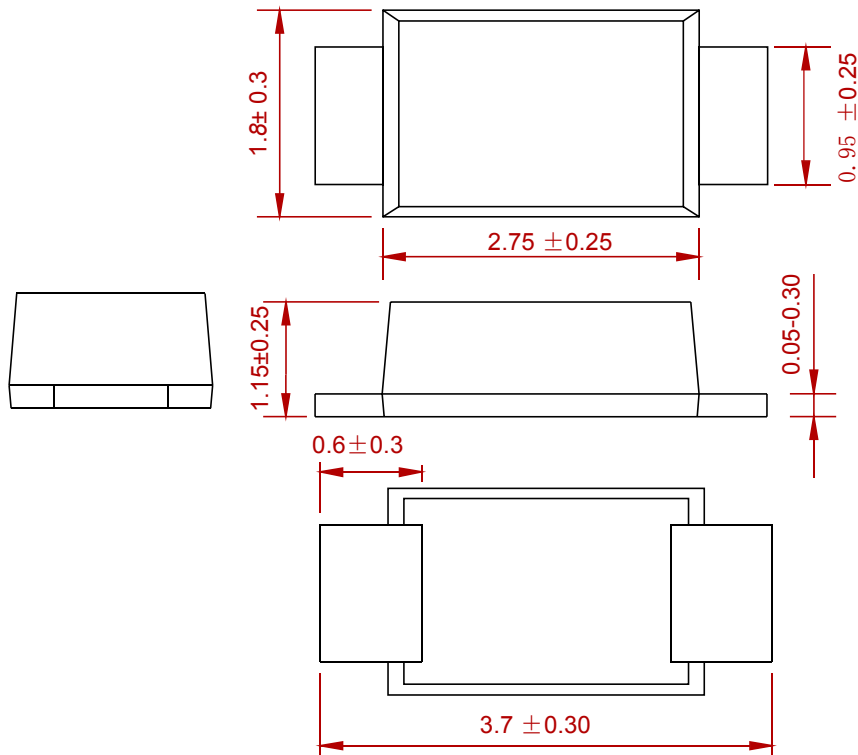


FIG.5-TYPICAL JUNCTION CAPACITANCE

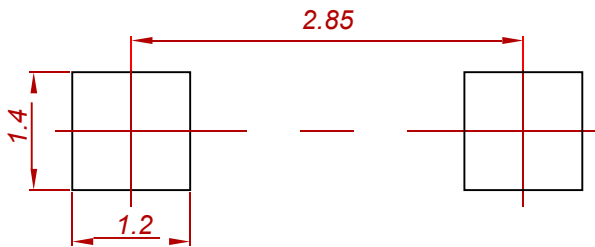


**PACKAGE MECHANICAL DATA**



*Dimensions in millimeters*

**Suggested Pad Layout**



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$  mm.
3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
FR101W THRU FR107W	SOD-123FL	3000

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